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Series expansion of the quantum admittance in mesoscopic systems

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The quantum admittance of an interacting/coupled mesoscopic system and its series expansion are obtained with the help of a refermionization procedure. It allows us to characterize the dependency of this quantity according to the applied dc voltage, temperature and frequency without restriction on the relative values of these variables. Explicit expressions of the admittance are derived in both small and large interaction/coupling limits, given a clear indication about the inductive or capacitive behavior of the mesoscopic system, first in the low temperature regime and second in the low frequency regime, allowing to identify the conditions to have a positive dephasing.

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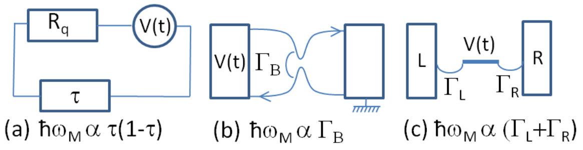
There is a growing interest regarding the quantum admittance from both experimental and theoretical points of view for the reason that this quantity contains in itself many information about the dynamics of mesoscopic systems: its real part provides the value of the low-frequency effective resistance and is related to the anti-symmetrized current fluctuations[1] (noise); its imaginary part brings indication about the inductive or capacitive nature of the system; moreover both its real and imaginary parts give the dephasing of the current response compared to the applied voltage modulation, and appear in the expression of the non-symmetrized noise[2] which is the relevant quantity in high frequency experiments.[3–6]

Measurement of quantum admittance has been achieved recently in two dimensional electron gas[7–10], carbon nanotube double quantum dot[11], supraconducting junction[12] and quantum dot coupled to a two dimensional electron gas.[13] A formalism to calculate the quantum admittance for non-interacting systems based on the scattering theory is available in the literature.[14–18] The effects of strong electron interactions on the admittance of a quantum dot coupled to an edge state has also been considered,[19] but distinct approaches were used to describe the perturbative regime (weak barrier case) and the non-perturbative one. Admittance of a double quantum dot has been calculated with an emphasis on the effective capacitance obtained in the low frequency limit.[20]

This Brief Report presents the calculation of the quantum admittance using a refermionization procedure which allows us to describe the full range of frequency, temperature, and voltage dependencies in various coupled or interacting mesoscopic systems (see Fig. 1) in an unified way. Indeed, our results apply to: (i) a one-channel conductor coupled to a measurement circuit whose resistance is equal to the quantum of resistance, an experimental configuration which is realizable with a quantum point contact;[21] (ii) a constriction in a two dimensional electron gas in the fractional quantum Hall regime with the specific filling factor $\nu = 1/2$, and (iii) a quantum dot coupled to two reservoirs.



(a) $\hbar\omega_M \propto \tau(1-\tau)$ (b) $\hbar\omega_M \propto \Gamma_B$ (c) $\hbar\omega_M \propto (\Gamma_L+\Gamma_R)$

FIG. 1: Pictures of (a) a one-channel conductor with transmission τ coupled to a resistance equal to the quantum of resistance $R_q = e^2/h$, (b) a constriction in a fractional quantum Hall bar with backscattering amplitude Γ_B, and (c) a double barriers quantum dot whose coupling amplitudes with the left (L) and right (R) reservoirs are denoted Γ_L and Γ_R, respectively. The associated characteristic energy, $\hbar\omega_M$, is indicated for each of these systems. $\nu = 1/2$ for systems (a) and (b), and $\nu = 1$ for system (c).

When a voltage modulation $V(t) = V_0 + V_\omega \cos(\omega t)$ is applied to an electronic circuit, the current becomes time-dependent and can be written as a series (photo-assisted current): $I(t) = \sum_{N=-\infty}^{\infty} I^{(N)}(\omega)e^{iN\omega t}$, where $I^{(N)}$ is the N^{th} harmonic of the current. By using the fact that the current is a real quantity, it can be written equivalently:

$$I(t) = I^{(0)} + 2\sum_{N=1}^{\infty} \mathrm{Re}\{I^{(N)}(\omega)e^{iN\omega t}\}\ . \qquad (1)$$

In the linear response regime, i.e. $e^*V_\omega \ll \{e^*V_0, \hbar\omega\}$ where $e^* = \nu e$ is the effective charge that travels through the mesoscopic system, the current reduces to:[22]

$$I(t) \approx I^{dc}(V_0) + 2\nu V_\omega \mathrm{Re}\{Y(\omega)e^{i\omega t}\}\ , \qquad (2)$$

where I^{dc} is the dc current associated to the application of a constant voltage V_0, and Y is the admittance defined as the derivative of the first harmonic of the current according to the amplitude of the voltage modulation: $Y(\omega) = \nu^{-1}\partial I^{(1)}(\omega)/\partial V_\omega$. The introduction of a coefficient ν allows us to treat in an unified way the three systems depicted on Fig. 1. From Eq. (2), it can be understand that the real part of the admittance, the conductance, gives the instantaneous response to the voltage modulation, whereas the imaginary part of the admittance, the susceptance, plays a role in the presence of dephasing only. Indeed, introducing the phase $\varphi(\omega) = \arctan[\mathrm{Im}\{Y(\omega)\}/\mathrm{Re}\{Y(\omega)\}]$, the current reads: $I(t) = I^{dc}(V_0) + 2\nu|Y(\omega)|V_\omega \cos(\omega t + \varphi(\omega))$. The method used below to get the admittance is to calculate the photo-assisted current, then to extract its first harmonic and finally to take its derivative according to V_ω.

The systems depicted on Fig. 1 are modelized within the framework of the Tomonaga-Luttinger theory,[23,24] i.e. with the Hamiltonian:[25]

$$H = \frac{\hbar v_F}{4\pi}\int_{-\infty}^{\infty} dx[(\partial_x\phi_-(x))^2 + (\partial_x\phi_+(x))^2] + \frac{\hbar\omega_M}{4\pi} e^{i[\phi_-(x)+\phi_+(x)]/\sqrt{2} - ie^*\chi(t)/(\hbar c)} + hc\ , \quad (3)$$

where ϕ_- and ϕ_+ are the bosonic fields associated to the left (-) and right (+) moving electrons, and v_F is the Fermi velocity. The function $\chi(t) = -c\int V(t)dt$ is included in order to treat the time-dependent applied voltage. The energy $\hbar\omega_M$ characterizes the mesoscopic system: (i) in the case where the mesoscopic system is coupled to a measurement circuit with a resistance equal to the quantum of resistance (see Fig. 1(a)), then $\hbar\omega_M \propto (1-\tau)\tau$, where τ is the transmission through the mesoscopic system, and $\nu = 1/2$ because the bias voltage seen by the mesoscopic system is $V(t)/2$;[2] (ii) in the case of a constriction in a two dimensional electron gas in the fractional quantum Hall regime with a filling factor $\nu = 1/2$ (see Fig. 1(b)), then $\hbar\omega_M \propto \Gamma_B$ where Γ_B is the backscattering amplitude;[26] (iii) in the case of a quantum dot coupled to left (L) and right (R) reservoirs with amplitudes Γ_L and Γ_R (see Fig. 1(c)), then $\hbar\omega_M \propto \Gamma_L + \Gamma_R$,[14] and $\nu = 1$. In the two first cases, the calculated current is the backscattering current whereas in the latter case, it is the flux of charges across the barriers.

The justification of Eq. (3) is obvious for the system (b) of Fig. 1 since the transport of the charges in such a system is done along the edge states of the Hall bar which have a one-dimensional character and thus are subject to Coulomb interactions that are well described within the Tomonaga-Luttinger theory.[25] The justification of Eq. (3) for the system (a) of Fig. 1 is based on the mapping that has been established between a one-channel conductor coupled to a measurement circuit and an impurity in a Luttinger liquid.[27] Successful description of transport properties has been recently achieved by this means.[2] Moreover, as the expression of the admittance obtained from Eq. (3) is identical to the one that has been obtained with the help of the scattering theory for the system (c) of Fig. 1,[14] it is possible to include it in the list of interacting/coupled systems that are described here.

From the Hamiltonian of Eq. (3), the photo-assisted current can be calculated with the help of a refermionization procedure[28] which has the great advantage to be an exact calculation with respect to the energy $\hbar\omega_M$. The first order harmonic of the ac current in the linear response regime with V_ω has been derived in Ref. 26. It

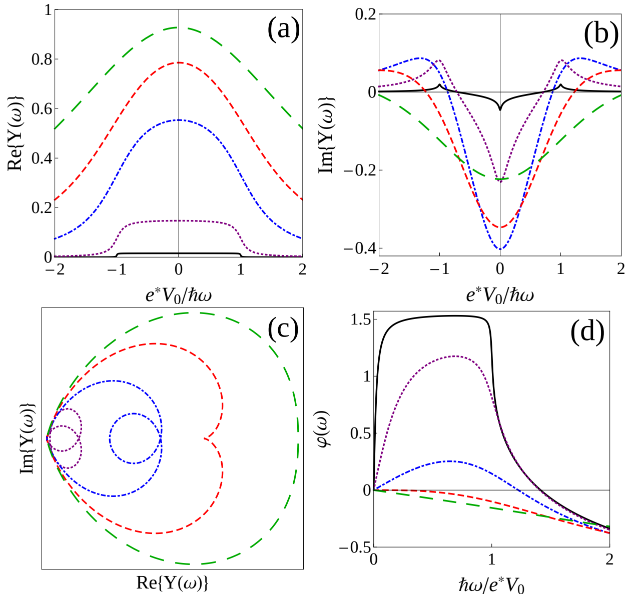


FIG. 2: (a) Real part, (b) imaginary part, (c) Nyquist graph, and (d) phase of the admittance at $T = 0$, for $\hbar\omega_M = 0.02e^*V_0$ (black solid line), $\hbar\omega_M = 0.2e^*V_0$ (purple dotted line), $\hbar\omega_M = e^*V_0$ (blue dash-dotted line), $\hbar\omega_M = 2e^*V_0$ (red dashed line) and $\hbar\omega_M = 4e^*V_0$ (green long dashed line). The black solid line in graph (c) in not plotted for reasons of visibility. Re$\{Y(\omega)\}$ and Im$\{Y(\omega)\}$ are plotted in units of $G_q = e^2/h$, the quantum of conductance.

leads to the admittance:

$$Y(\omega) = \frac{e^2}{2\hbar\omega}\int_{-\infty}^{\infty}\left[f(\hbar\Omega + e^*V_0) - f(-\hbar\Omega + e^*V_0)\right] \times\left[t(\Omega) - t(\Omega-\omega)\right]d\Omega\ , \quad (4)$$

where f is the Fermi-Dirac distribution function, and $t(\Omega) = (i\omega_M/2)/(\Omega + i\omega_M/2)$ is the transmission amplitude of the one-channel conductor for Fig. 1(a), of the constriction for Fig. 1(b), or of the barriers for Fig. 1(c). To characterize its low frequency behavior, it is useful to expand the admittance in powers of ω under the form: $Y(\omega) = \sum_{n=0}^{\infty} Y^{(n)}\omega^n$. Starting from Eq. (4) and using the relation: $t(\Omega-\omega) = \sum_{n=0}^{\infty}(2\omega)^n t^{n+1}(\Omega)/(i\omega_M)^n$, the harmonics of the admittance can be written as:

$$Y^{(n)} = -\frac{2^n e^2}{h(i\omega_M)^{n+1}}\int_{-\infty}^{\infty}[t(\Omega)]^{n+2} \times\left[f(\hbar\Omega + e^*V_0) - f(-\hbar\Omega + e^*V_0)\right]d\Omega\ , \quad (5)$$

which is purely real for odd values of n and purely imaginary for even values of n. Eqs. (4) and (5) are the central results of this Brief Report since they allow us to calculate the admittance, and all the coefficients of its expansion in powers of ω, whatever the dc voltage V_0, temperature T, and frequency ω_M are. In the following, the behavior of the admittance in various regimes is discussed looking at the combined effects of $\hbar\omega_M$, e^*V_0, $\hbar\omega$, and k_BT.

At zero temperature, the integration over frequency in Eq. (4) can be performed explicitly:

$$Y_{T=0}(\omega) \;=\; \frac{e^2}{4ih}\frac{\omega_M}{\omega}\sum_{\pm}\ln\left(1+\frac{i\hbar\omega}{\hbar\omega_M/2\pm ie^*V_0}\right)\;. \tag{6}$$

This result coincides with the one obtained with the help of scattering theory in the case of a double barriers quantum dot,[14,18] and it obeys the simple relation:[2,29,30] $\mathrm{Re}\{Y(\omega)\} = e\sum_{\pm} I^{dc}(V_0 \pm \hbar\omega/e^*)/(2\hbar\omega)$. The associated coefficients of the series expansion read as:

$$Y^{(n)}_{T=0} \;=\; \frac{e^2}{4h}\sum_{\pm}\frac{(-i)^n\hbar^{n+1}\omega_M}{(n+1)(\hbar\omega_M/2\pm ie^*V_0)^{n+1}}\;. \tag{7}$$

In Fig. 2(a) is plotted the real part of the admittance at zero temperature as a function of voltage. Steps are observed at positions $e^*V_0 = \pm\hbar\omega$ (see the black solid line and the purple dotted line) which disappear when $\hbar\omega_M$ increases. The profile of the imaginary part of the admittance shown in Fig. 2(b) is in agreement with recent experimental data[12] which confirms that the distance between the two peaks observed for small $\hbar\omega_M$ is equal to $2\hbar\omega$. Fig. 2(c) reveals interesting features which highlight the fact that the regimes of small and large $\hbar\omega_M$ differ fundamentally. Indeed, in the limit $\hbar\omega_M \gg e^*V_0$, the Nyquist graph is a quasi-circle (see the green long dashed line of Fig. 2(c)) which means that the admittance is a function of a complex variable z with a single pole z_p of order 1, i.e. of the form: $(z-z_p)^{-1}$. When $\hbar\omega_M$ decreases, singularities and loops appear (see the red dashed line, the blue dash-dotted line and the purple dotted line of Fig. 2(c)) which mean that the admittance is a complex function with a single pole of higher order. As a consequence, the sign of the phase of the admittance will change when ω varies. It is precisely what it is observed in Fig. 2(d) which shows the phase of the admittance as a function of frequency. The sign of the phase gives indication about the inductive (i.e. $\varphi(\omega) < 0$) or capacitive (i.e. $\varphi(\omega) > 0$) character of the mesoscopic system. For small value of $\hbar\omega_M$ and for frequency inside the interval $[-e^*V_0/\hbar, e^*V_0/\hbar]$, the current is in phase opposition in comparison to the ac voltage since $\varphi(\omega) \approx \pi/2$ (see the black solid line) and the mesoscopic system acts as a capacitance. At large frequency, the system becomes inductive whatever the value of $\hbar\omega_M$ is. This frequency dependent profile of the phase is in qualitative agreement with experimental data obtained recently in carbon nanotube.[11]

	$\hbar\omega_M \approx 0$	$\hbar\omega_M \gg \{k_BT, \lvert e^*V_0\rvert, \lvert\hbar\omega\rvert\}$
$k_BT \ll \lvert e^*V_0\rvert$ and $\hbar\omega \approx 0$	$Y(\omega) = G_q\left(\frac{\hbar\omega_M}{2e^*V_0}\right)^2\left(1+i\frac{\omega}{\omega_M}\right)$ $\Rightarrow$ RC circuit in parallel $R^{-1}_{\mathrm{eff}} = G_q\left(\frac{\hbar\omega_M}{2e^*V_0}\right)^2$, $C^{-1}_{\mathrm{eff}} = \omega_M R_{\mathrm{eff}}$	$Y(\omega) = G_q\left(1-i\frac{\omega}{\omega_M}\right)$ $\Rightarrow$ RL circuit in series $R^{-1}_{\mathrm{eff}} = G_q$, $L^{-1}_{\mathrm{eff}} = \omega_M G_q$
$k_BT \gg \lvert e^*V_0\rvert$ and $\hbar\omega \approx 0$	$Y(\omega) = G_q\frac{\pi\hbar\omega_M}{8k_BT}\left(1-i\frac{\hbar\omega}{4k_BT}\right)$ $\Rightarrow$ RL circuit in series $R^{-1}_{\mathrm{eff}} = G_q\frac{\pi\hbar\omega_M}{8k_BT}$, $L^{-1}_{\mathrm{eff}} = \pi\omega_M G_q/2$	
$k_BT \ll \lvert e^*V_0\rvert \ll \lvert\hbar\omega\rvert$	$Y(\omega) = G_q\frac{\omega_M}{4\omega}\left[\pi\mathrm{sign}(\omega) - i\ln\left(\frac{(\hbar\omega)^2}{(\hbar\omega_M/2)^2+(e^*V_0)^2}\right)\right]$ $\Rightarrow$ RL circuit in parallel $R^{-1}_{\mathrm{eff}} = G_q\frac{\pi\omega_M}{4\lvert\omega\rvert}$,$L^{-1}_{\mathrm{eff}} = \frac{G_q\omega_M}{4}\ln\left(\frac{(\hbar\omega)^2}{(\hbar\omega_M/2)^2+(e^*V_0)^2}\right)$	

TABLE I: Admittance $Y(\omega)$ and its associated effective resistance and inductance/capacitance in various limits. $G_q = e^2/h$ refers to the quantum of conductance.

Next, in the framework of the low frequency regime and with the help of Eq. (5) the admittance is calculated at finite temperature up to the first order in ω, including the terms $n=0$ and $n=1$ in the sum over n. The results are summarized in Tab. I. Again, it is interesting to interpret them in term of an effective RLC circuit. At large $\hbar\omega_M$, since $\varphi(\omega) < 0$, the mesoscopic system is inductive whatever the temperature is: the mesoscopic system behaves as a RL circuit in series with an effective resistance which is independent of any characteristic energy: $R_{\mathrm{eff}} = G_q^{-1}$, and an effective inductance which is dependent of ω_M only: $L_{\mathrm{eff}} = (\omega_M G_q)^{-1}$. Note that the admittance converges to the value G_q at very high $\hbar\omega_M$.

At small $\hbar\omega_M$, the dynamic of the mesoscopic system is strongly temperature dependent: at low temperature in comparison to the voltage, the system is capacitive

($\varphi(\omega) > 0$) whereas it is inductive ($\varphi(\omega) < 0$) at larger temperature. The fact that at zero temperature a change from capacitive to inductive circuit is observed when $\hbar\omega_M$ increases is in agreement with what was obtained in Ref. 14 for a double barriers quantum dot. Indeed, at small coupling $\hbar\omega_M \propto \Gamma_L + \Gamma_R$, this system is capacitive because of the low value of the transmission coefficient equal to $\mathcal{T}(\Omega) = t(\Omega)t^*(\Omega)$, with no possibility of activation by any energy since temperature and frequencies are all small. It is interesting to notice that in the limit $\hbar\omega_M \approx 0$, the expression of the effective resistance, R_{eff}, contains always the interaction/coupling energy, $\hbar\omega_M$, and the largest of the three other characteristic energies, i.e. either k_BT, e^*V_0 or $\hbar\omega$. Indeed, at high temperature: $G_qR_{\text{eff}} = 8k_BT/(\pi\hbar\omega_M)$, in agreement with Ref. 31; at high voltage: $G_qR_{\text{eff}} = (2e^*V_0)^2/(\hbar\omega_M)^2$; and at high frequency: $G_qR_{\text{eff}} = 4\omega/(\pi\omega_M)$. Furthermore, at high temperature and whatever the value of $\hbar\omega_M$ is, the effective resistivity reads as:

$$R_{\text{eff}}^{-1} = \frac{\partial I^{dc}(V_0)}{\partial V_0} = \frac{e^2\hbar\omega_M}{16\pi h k_B T}\Psi'\left(\frac{1}{2} + \frac{\hbar\omega_M}{8\pi k_B T}\right) , \quad (8)$$

where Ψ is the Digamma function, in agreement with Ref. 32.

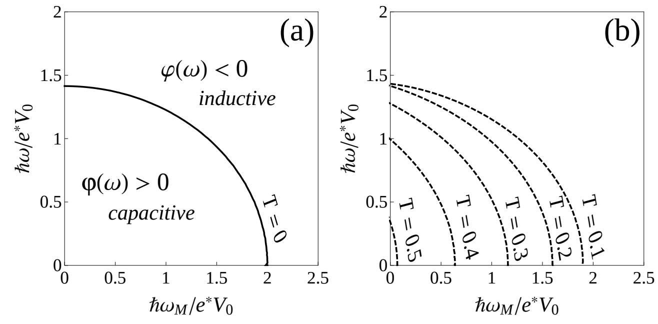


FIG. 3: (a) Sign of the phase of the admittance at zero temperature as a function of coupling/interaction $\hbar\omega_M$ and ac frequency $\hbar\omega$. (b) Evolution of the frontier between regions of positive and negative signs when temperature T increases (in units of e^*V_0/k_B).

In order to understand the relative effects of the various energies that characterize the system, is plotted in Fig. 3 the frontier between regions of positive and negative phases as a function of $\hbar\omega_M/(e^*V_0)$ and $\hbar\omega/(e^*V_0)$. At zero temperature, the equation for the frontier can be extracted from Eq. (6), it reads as: $|\hbar\omega| = \sqrt{2[(e^*V_0)^2 - (\hbar\omega_M/2)^2]}$. Below this curve, the phase is positive whereas beyond it, the phase is negative (see Fig. 3(a)). This frontier moves towards the origin when the temperature increases (see Fig. 3(b)). It allows us to conclude that to get a positive value for the phase, i.e. a capacitive behavior of the mesoscopic system, the temperature and characteristic frequencies have to be small enough in comparison to the dc voltage, more precisely, one must have: $\hbar\omega_M/2 \lesssim |e^*V_0|$, $|\hbar\omega| \lesssim \sqrt{2[(e^*V_0)^2 - (\hbar\omega_M/2)^2]}$, and $k_BT \lesssim |e^*V_0|$.

In summary, the quantum admittance associated to an impurity in a Tomonaga-Luttinger liquid with $\nu = 1/2$ has been calculated with the help of a refermionization procedure. Its expression is identical to the one of a double barrier quantum dot derived in the framework of the scattering theory.[14] Furthermore, in light of the mapping of Ref. 27, it is possible to consider in an unified view the three systems depicted in Fig. 1. A detailed analysis of their admittance has shown that if at least one of the characteristic energies is larger than the dc applied voltage, the mesoscopic system behaves has an inductance since it is activated by either temperature, frequency or interaction/coupling frequency.

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